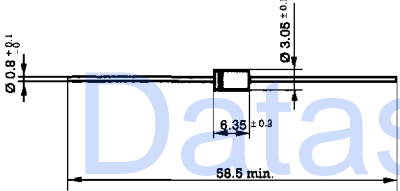



2 Amp. Glass Passivated Avalanche Ultrafast Diode

<p>Dimensions in mm.</p> <p style="text-align: right;">DO-15 (Plastic)</p> 	<p>Voltage 50 to 400 V.</p> <p>Current 2 A at 55 °C.</p> 
<p>Mounting instructions</p> <ol style="list-style-type: none"> 1. Min. distance from body to soldering point, 4 mm. 2. Max. solder temperature, 350 °C. 3. Max. soldering time, 3.5 sec. 4. Do not bend lead at a point closer than 2 mm. to the body. 	<ul style="list-style-type: none"> • Glass Passivated Junction • High current capability • The plastic material carries U/L recognition 94 V-0 • Terminals: Axial Leads • Polarity: Color band denotes cathode

Maximum Ratings, according to IEC publication No. 134

		EGP20A	EGP20B	EGP20D	EGP20F	EGP20G
V_{RRM}	Peak Recurrent reverse voltage (V)	50	100	200	300	400
V_{RMS}	Maximum RMS voltage	35	70	140	210	280
V_{DC}	Maximum DC blocking voltage	50	100	200	300	400
$I_{F(AV)}$	Forward current at Tamb = 55 °C	2 A				
I_{FRM}	Recurrent peak forward current	20 A				
I_{FSM}	8.3 ms. peak forward surge current (Jedec Method)	75 A				
t_{rr}	Max. reverse recovery time from $I_F = 0.5 A$; $I_R = 1 A$; $I_{RR} = 0.25 A$	50 ns				
C_j	Typical Junction Capacitance at 1 MHz and reverse voltage of $4V_{DC}$	45 pF			30 pF	
T_j	Max. operating temperature	+ 150 °C				
T_{stg}	Storage temperature range	- 65° to + 150 °C				
E_{RSM}	Maximum non repetitive peak reverse avalanche energy. $I_R = 1 A$; $T_j = 25 °C$	20 mJ				

Electrical Characteristics at Tamb = 25 °C

V_f	Max. forward voltage drop at $I_F = 2 A$	0.95 V	1.25 V
I_R	Max. reverse current at V_{RRM} at 25 °C at 150 °C	5 μA 50 μA	
R_{thj-a}	Max. thermal resistance (l = 10 mm.)	30 °C/W	

Rating And Characteristic Curves

